

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of producing an alumina film mainly in alpha crystal structure on a substrate wherein the substrate optionally has ~~(including a substrate having a film previously formed thereon thereon)~~, comprising:

treating the surface of the substrate with a ceramic powder mainly having a crystal structure which is the same as ~~[[that]]~~ the crystal structure of alumina in the alpha crystal structure to form fine scratches on the surface of the substrate; ~~and then~~

washing away the ceramic powder to leave the fine scratches on the surface of the substrate; and then

depositing the alumina film mainly in alpha crystal structure on the substrate.

Claim 2 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein the ceramic powder is an alumina powder in alpha crystal structure.

Claim 3 (Previously Presented): The method of producing the alumina film according to Claim 2, wherein the alumina powder has an average particle diameter of 50 μm or less.

Claim 4 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein the substrate has a film formed on the surface thereof made of one or more compounds selected from the group consisting of compounds of one or more elements selected from the group consisting of elements in Groups 4a, 5a and 6a in the periodic table, Al, Si and Y with one or more elements of C, N, B, and O; the solid solutions thereof; and compounds of one or more elements of C, N, and B.

Claim 5 (Previously Presented): The method of producing the alumina film according to Claim 4, wherein the substrate has a hard film formed on the surface thereof comprising one or more compounds selected from the group consisting of TiN, TiC, TiCN, TiAlN and TiAlCrN.

Claim 6 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein treating the substrate surface comprises polishing the substrate surface with the ceramic powder.

Claim 7 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein treating the substrate surface comprises immersing and ultrasonically treating the substrate in a liquid in which the ceramic powder is dispersed.

Claim 8 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein depositing the alumina film comprises a gas-phase growth method.

Claim 9 (Previously Presented): The method of producing the alumina film according to Claim 8, wherein the gas-phase growth method is a method selected from the group consisting of CVD, PE-CVD, sputtering, ion plating and vapor deposition.

Claim 10 (Previously Presented): A method of producing a laminated film-coated part, comprising depositing an alumina film mainly in alpha crystal structure on the film previously formed on the substrate according to Claim 1.

Claim 11 (Currently Amended): A method of producing a laminated film-coated part comprising an alumina film namely in alpha crystal structure, comprising: forming a hard film containing one or more compounds selected from the group consisting of TiN, TiC, TiCN, TiAlN and TiAlCrN on a substrate, treating a surface of the hard film with a ceramic powder mainly having a crystal structure which is the same as ~~[[that]]~~the crystal structure of alumina in the alpha crystal structure to form fine scratches on the surface of the hard film, washing away the ceramic powder to leave the fine scratches on the surface of the hard film, and then depositing an alumina film mainly in alpha crystal structure on the hard film after the surface treatment with said ceramic powder.

Claim 12 (Canceled).

Claim 13 (Previously Presented): The method of producing the alumina film according to Claim 1, comprising depositing the alumina film mainly in alpha crystal structure at a temperature of 650 to 800°C.

Claim 14 (Previously Presented): The method of producing the alumina film according to Claim 1, further comprising oxidizing the substrate at a temperature of 650 to 800°C prior to depositing the alumina film on the substrate.

Claim 15 (Previously Presented): The method of producing the alumina film according to Claim 2, wherein the alumina powder has an average particle diameter of 1 μm or less.

Claim 16 (Previously Presented): The method of producing the alumina film according to Claim 1, wherein the thickness of the alumina film is in a range of 0.1 μm to 20 μm .

Claim 17 (Previously Presented): The method of producing an alumina film according to Claim 1, wherein the thickness of the alumina film is in a range of 1 μm to 5 μm .

Claim 18 (Currently Amended): The method of producing an alumina film mainly in alpha crystal structure on a substrate wherein the substrate optionally has ~~(including a substrate having a film previously formed thereon thereon)~~ according to Claim 1, comprising:

treating the surface of the substrate with a ceramic powder mainly having a crystal structure which is the same as ~~[[that]]~~ the crystal structure of alumina in the alpha crystal structure to form fine scratches on the surface of the substrate; ~~and then~~

washing away the ceramic powder to leave the fine scratches on the surface of the substrate; and then

depositing the alumina film mainly in alpha crystal structure at a temperature of 650 to 800°C on the substrate by a gas-phase growth method selected from the group consisting of CVD, PE-CVD, sputtering, ion plating and vapor deposition.

Claim 19 (Previously Presented) : The method of producing an alumina film mainly in alpha crystal structure on a substrate (including a substrate having a film previously formed thereon) according to Claim 1, wherein an oxygen pressure during depositing the alumina film mainly in alpha crystal structure on the substrate, is 0.75 Pa or less.